

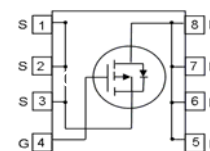
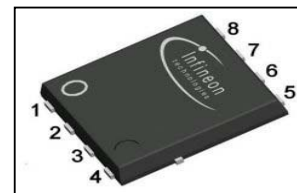
OptiMOS™ P3 Power-Transistor
Features

- single P-Channel in SuperSO8
- Qualified according JEDEC¹⁾ for target applications
- 150 °C operating temperature
- 100% Avalanche tested
- $V_{GS}=25$ V, specially suited for notebook applications
- Pb-free; RoHS compliant
- applications: battery management, load switching
- Halogen-free according to IEC61249-2-21


Product Summary

V_{DS}	-30	V
$R_{DS(on),max}$	8.4	m Ω
I_D	-78.6	A

PG-TDSON-8



Type	Package	Marking	Lead free	Halogen free	Packing
BSC084P03NS3 G	PG-TDSON-8	084P3NS	Yes	Yes	non dry

Maximum ratings, at $T_j=25$ °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	$T_C=25$ °C	-78.6	A
		$T_C=70$ °C	-62.9	
		$T_A=25$ °C	-14.9	
Pulsed drain current	$I_{D,pulse}$	$T_C=25$ °C ³⁾	-200	
Avalanche energy, single pulse	E_{AS}	$I_D=-50$ A, $R_{GS}=25$ Ω	105	mJ
Gate source voltage	V_{GS}		± 25	V
Power dissipation	P_{tot}	$T_C=25$ °C	69	W
		$T_A=25$ °C ²⁾	2.5	
Operating and storage temperature	T_j, T_{stg}		-55 ... 150	°C
ESD class		JESD22-A114 HBM	1C (1-2 kV)	
Soldering temperature			260	°C
IEC climatic category; DIN IEC 68-1			55/150/56	

¹⁾ J-STD20 and JESD22

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}		-	-	1.8	K/W
Thermal resistance, junction - ambient	R_{thJA}	6 cm ² cooling area ²⁾	-	-	50	

Electrical characteristics, at $T_j=25\text{ }^\circ\text{C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}, I_D=-250\text{ }\mu\text{A}$	-30	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-105\text{ }\mu\text{A}$	-3.1	-2.5	-1.9	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=-30\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ }^\circ\text{C}$	-	-	-1	μA
		$V_{DS}=-30\text{ V}, V_{GS}=0\text{ V}, T_j=125\text{ }^\circ\text{C}$	-	-	-100	
Gate-source leakage current	I_{GSS}	$V_{GS}=-25\text{ V}, V_{DS}=0\text{ V}$	-	-	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=-6\text{ V}, I_D=-30\text{ A}$	-	8.4	14.0	m Ω
		$V_{GS}=-10\text{ V}, I_D=-50\text{ A}$	-	6.1	8.4	
Gate resistance	R_G		-	2.2	-	Ω
Transconductance	g_{fs}	$ V_{DS} >2 I_D R_{DS(on)max}, I_D=-50\text{ A}$	33	66	-	S

²⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

³⁾ See Fig. 3

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics

Input capacitance	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=-15\text{ V},$ $f=1\text{ MHz}$	-	3190	4785	pF
Output capacitance	C_{oss}		-	1520	2280	
Reverse transfer capacitance	C_{rss}		-	110	165	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=-15\text{ V}, V_{GS}=-10\text{ V}, I_D=-50\text{ A},$ $R_G=6\ \Omega$	-	16	25	ns
Rise time	t_r		-	134	200	
Turn-off delay time	$t_{d(off)}$		-	33	50	
Fall time	t_f		-	8	12	

Gate Charge Characteristics³⁾

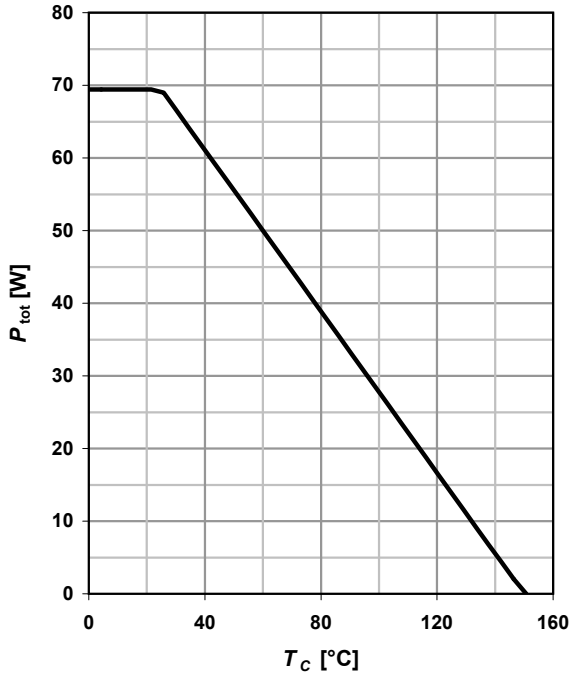
Gate to source charge	Q_{gs}	$V_{DD}=-15\text{ V}, I_D=-50\text{ A},$ $V_{GS}=0\text{ to }-10\text{ V}$	-	15	20	nC
Gate charge at threshold	$Q_{g(th)}$		-	5	7	
Gate to drain charge	Q_{gd}		-	7	11	
Switching charge	Q_{sw}		-	17	24	
Gate charge total	Q_g		-	43	58	
Gate plateau voltage	$V_{plateau}$		-	4.7	-	V
Output charge	Q_{oss}	$V_{DD}=-15\text{ V}, V_{GS}=0\text{ V}$	-	35	46	nC

Reverse Diode

Diode continuous forward current	I_S	$T_C=25\text{ }^\circ\text{C}$	-	-	78	A
Diode pulse current	$I_{S,pulse}$		-	-	200	
Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=-50\text{ A},$ $T_j=25\text{ }^\circ\text{C}$	-	-	-1.1	V
Reverse recovery time	t_{rr}	$V_R=15\text{ V}, I_F= I_S ,$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	45	-	ns
Reverse recovery charge	Q_{rr}		-	50	-	nC

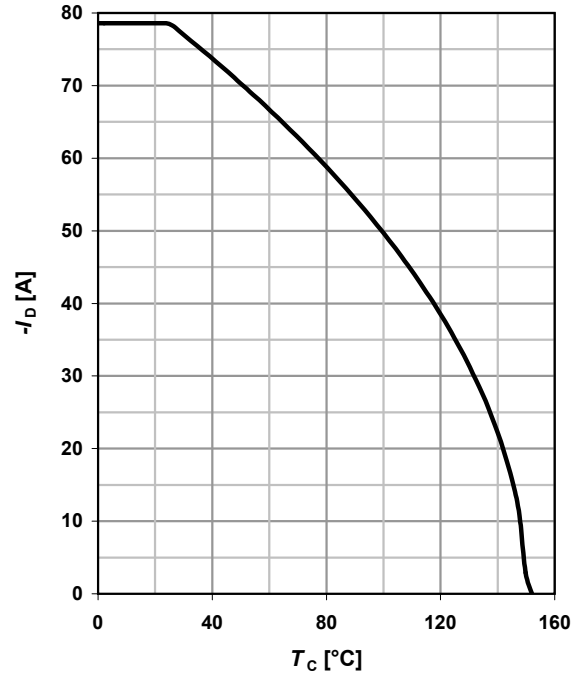
1 Power dissipation

$$P_{tot} = f(T_c)$$



2 Drain current

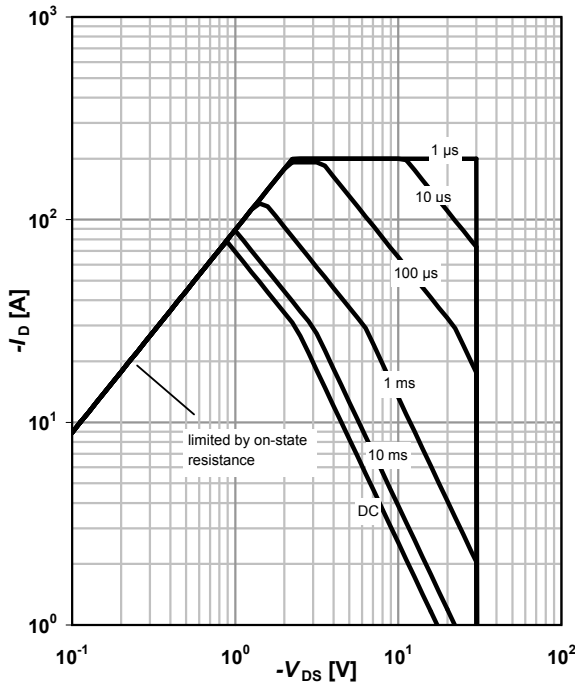
$$I_D = f(T_c); |V_{GS}| \geq 10 \text{ V}$$



3 Safe operating area

$$I_D = f(V_{DS}); T_c = 25 \text{ °C}^1; D = 0$$

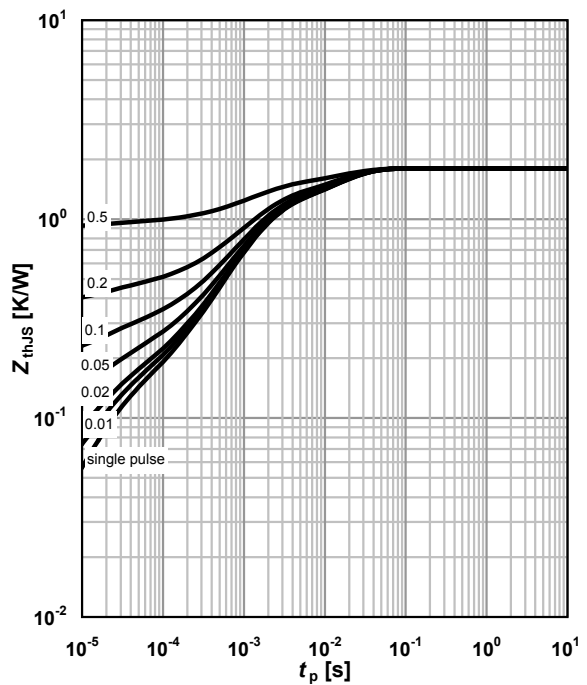
parameter: t_p



4 Max. transient thermal impedance

$$Z_{thJS} = f(t_p)$$

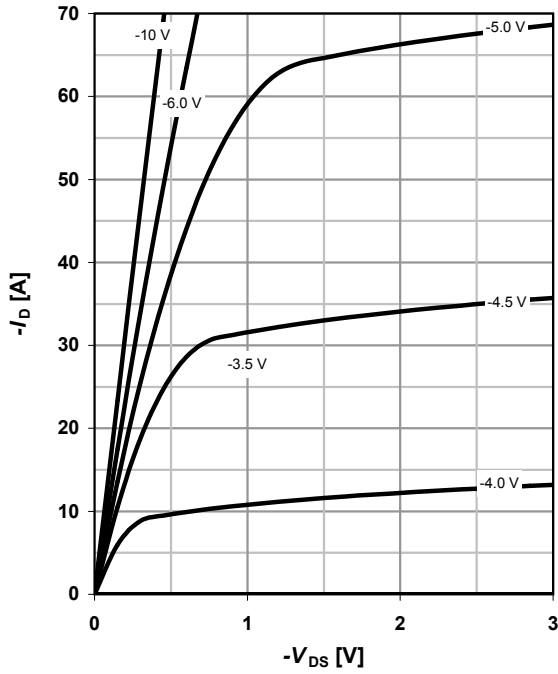
parameter: $D = t_p/T$



5 Typ. output characteristics

$I_D = f(V_{DS}); T_j = 25\text{ }^\circ\text{C}$

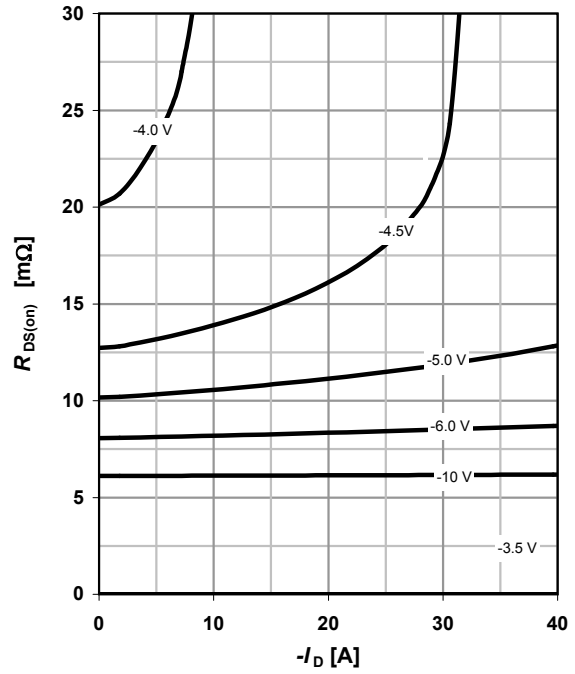
parameter: V_{GS}



6 Typ. drain-source on resistance

$R_{DS(on)} = f(I_D); T_j = 25\text{ }^\circ\text{C}$

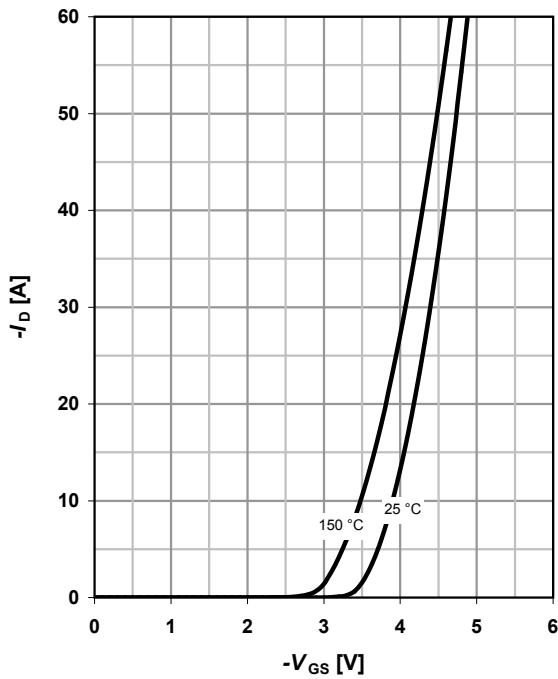
parameter: V_{GS}



7 Typ. transfer characteristics

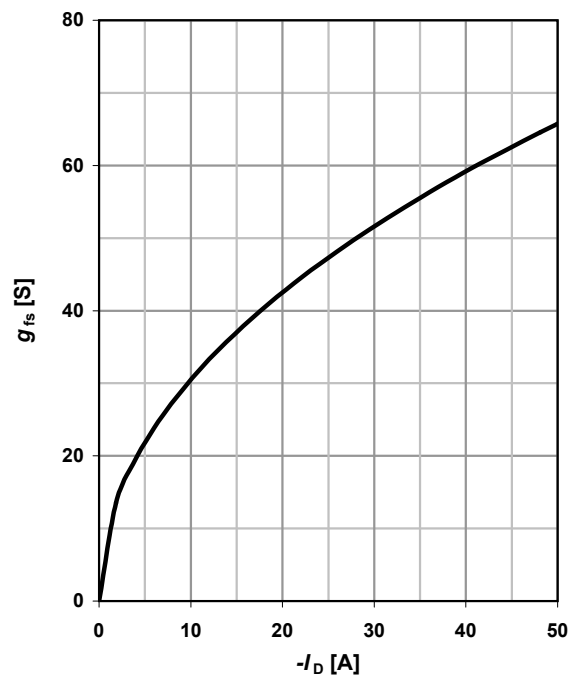
$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

parameter: T_j



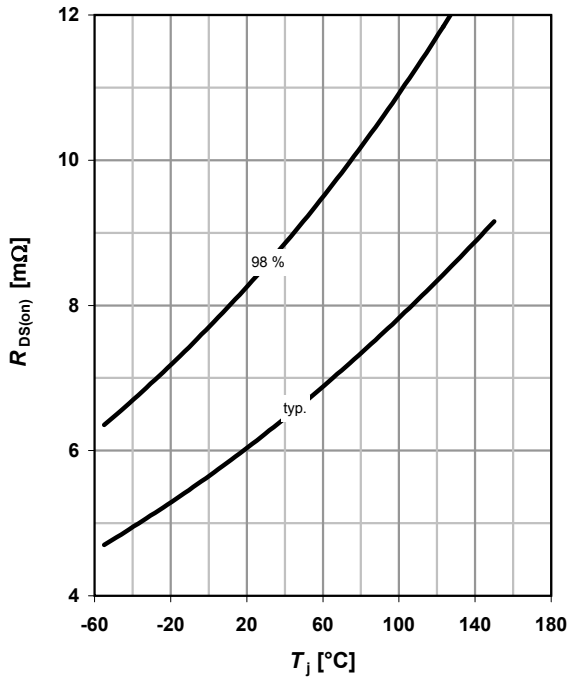
8 Typ. forward transconductance

$g_{fs} = f(I_D); T_j = 25\text{ }^\circ\text{C}$



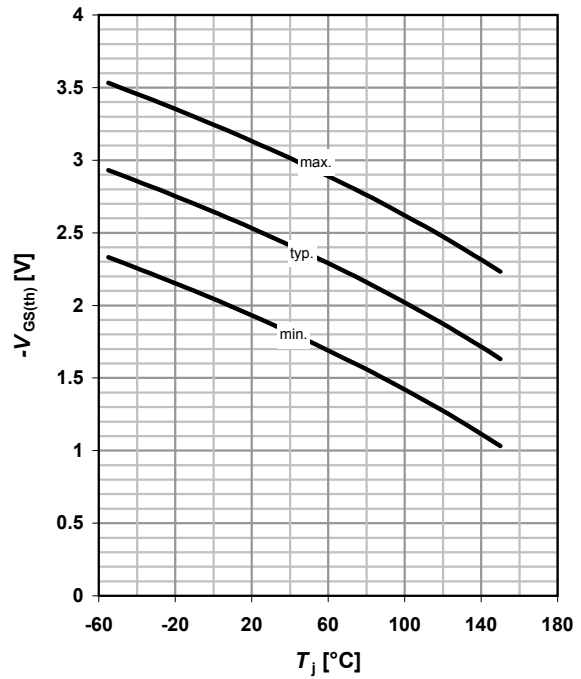
9 Drain-source on-state resistance

$R_{DS(on)} = f(T_j); I_D = -30 \text{ A}; V_{GS} = -10 \text{ V}$



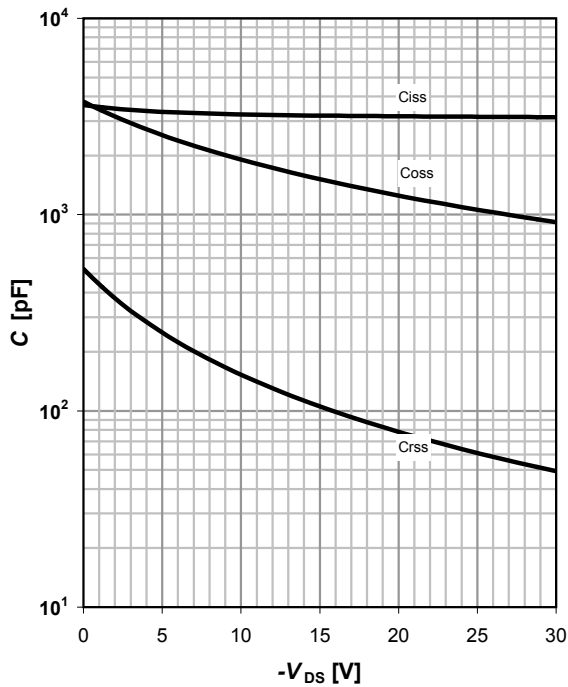
10 Typ. gate threshold voltage

$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}; I_D = -105 \mu\text{A}$



11 Typ. capacitances

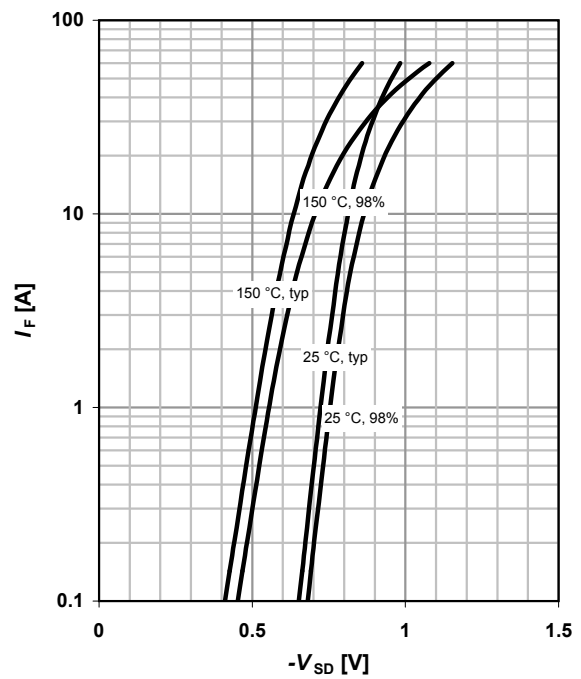
$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$



12 Forward characteristics of reverse diode

$I_F = f(V_{SD})$

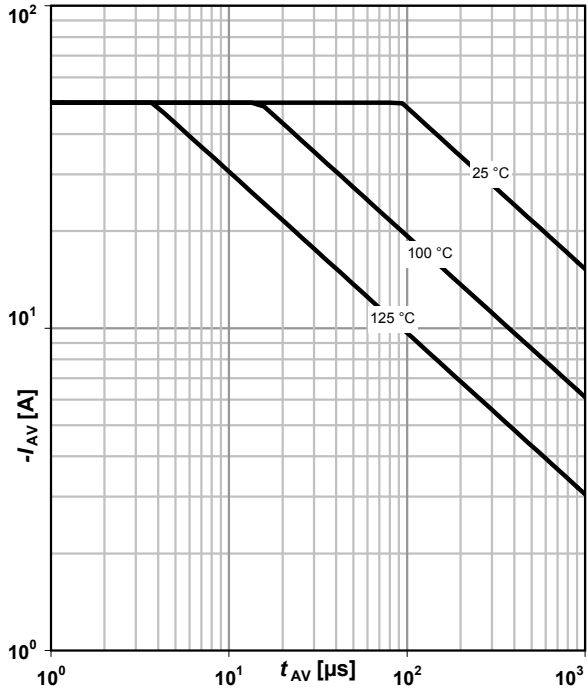
parameter: T_j



13 Avalanche characteristics

$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$

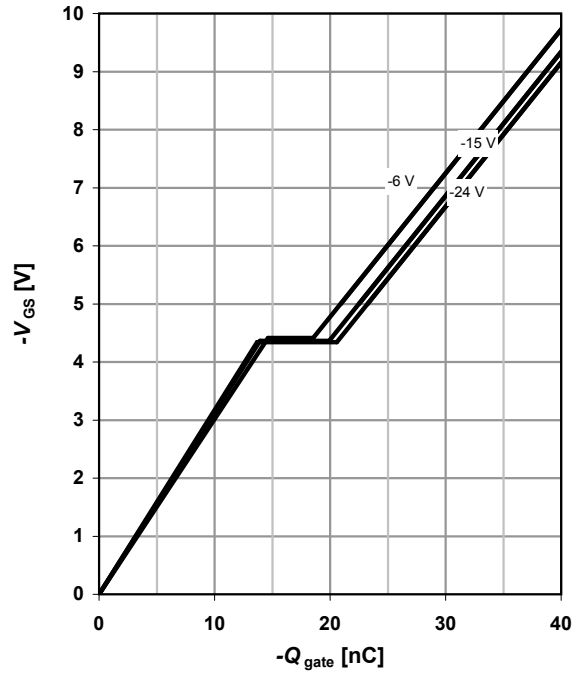
parameter: $T_{j(start)}$



14 Typ. gate charge

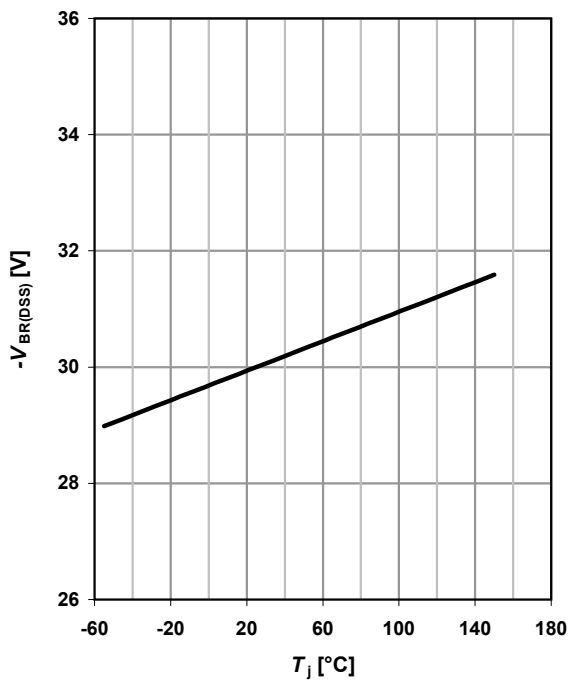
$V_{GS}=f(Q_{gate}); I_D=-50 \text{ A pulsed}$

parameter: V_{DD}

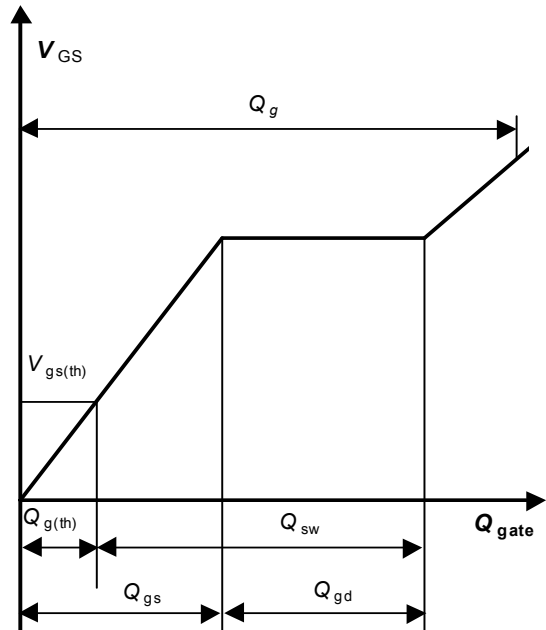


15 Drain-source breakdown voltage

$V_{BR(DSS)}=f(T_j); I_D=-250 \mu\text{A}$

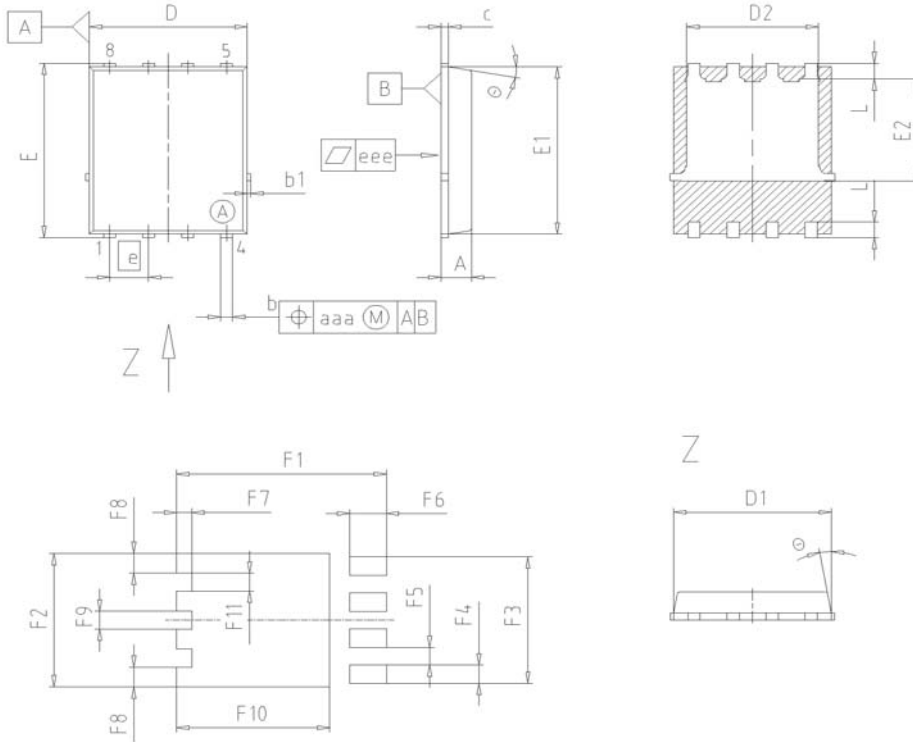


16 Gate charge waveforms



Package Outline

PG-TDSON-8



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.90	1.10	0.035	0.043
b	0.34	0.54	0.013	0.021
b1	0.02	0.22	0.001	0.008
c	0.15	0.35	0.006	0.014
D=D1	4.95	5.35	0.195	0.211
D2	4.20	4.40	0.165	0.173
E	5.95	6.35	0.234	0.250
E1	5.70	6.10	0.224	0.240
E2	3.40	3.80	0.134	0.150
e	1.27		0.050	
n	8		8	
L	0.45	0.65	0.018	0.026
□	8.5°	11.5°	8.5°	11.5°
aaa	0.25		0.010	
eee	0.05		0.002	
F1	6.75	6.95	0.266	0.274
F2	4.60	4.80	0.181	0.189
F3	4.36	4.56	0.172	0.180
F4	0.55	0.75	0.022	0.030
F5	0.52	0.72	0.020	0.028
F6	1.10	1.30	0.043	0.051
F7	0.40	0.60	0.016	0.024
F8	0.60	0.80	0.024	0.031
F9	0.53	0.73	0.021	0.029
F10	4.90	5.10	0.193	0.201
F11	0.53	0.73	0.021	0.029

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